

UNR521x Series (UN521x Series)

Silicon NPN epitaxial planar type

For digital circuits

■ Features

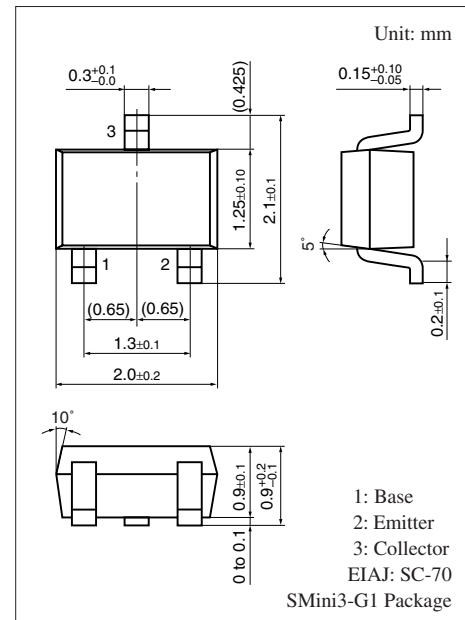
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts
- S-Mini type package, allowing automatic insertion through the tape packing and magazine packing

■ Resistance by Part Number

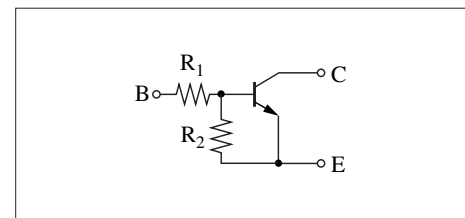
		Marking symbol (R ₁)	(R ₂)	
• UNR5210 (UN5210)	8L	47 kΩ	—	
• UNR5211 (UN5211)	8A	10 kΩ	10 kΩ	
• UNR5212 (UN5212)	8B	22 kΩ	22 kΩ	
• UNR5213 (UN5213)	8C	47 kΩ	47 kΩ	
• UNR5214 (UN5214)	8D	10 kΩ	47 kΩ	
• UNR5215 (UN5215)	8E	10 kΩ	—	
• UNR5216 (UN5216)	8F	4.7 kΩ	—	
• UNR5217 (UN5117)	8H	22 kΩ	—	
• UNR5218 (UN5218)	8I	0.51 kΩ	5.1 kΩ	
• UNR5219 (UN5219)	8K	1 kΩ	10 kΩ	
• UNR521D (UN521D)	8M	47 kΩ	10 kΩ	
• UNR521E (UN521E)	8N	47 kΩ	22 kΩ	
• UNR521F (UN521F)	8O	4.7 kΩ	10 kΩ	
• UNR521K (UN521K)	8P	10 kΩ	4.7 kΩ	
• UNR521L (UN521L)	8Q	4.7 kΩ	4.7 kΩ	
• UNR521M (UN521M)	EL	2.2 kΩ	47 kΩ	
• UNR521N (UN521N)	EX	4.7 kΩ	47 kΩ	
• UNR521T (UN521T)	EZ	22 kΩ	47 kΩ	
• UNR521V (UN521V)	FD	2.2 kΩ	2.2 kΩ	
• UNR521Z (UN521Z)	FF	4.7 kΩ	22 kΩ	

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	50	V
Collector-emitter voltage (Base open)	V _{CEO}	50	V
Collector current	I _C	100	mA
Total power dissipation	P _T	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C



Internal Connection



Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	
Emitter-base cutoff current (Collector open)	UNR5210/5215/5216/5217	$V_{EB} = 6 \text{ V}, I_C = 0$			0.01	mA
	UNR5213				0.1	
	UNR5212/5214/521D/ 521E/521M/521N/521T				0.2	
	UNR521Z				0.4	
	UNR5211				0.5	
	UNR521F/521K				1.0	
	UNR5219				1.5	
	UNR5218/521L/521V				2.0	
Forward current transfer ratio	UNR521V	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	6		20	—
	UNR5218/521K/521L		20			
	UNR5219/521D/521F		30			
	UNR5211		35			
	UNR5212/521E		60			
	UNR521Z		60	200		
	UNR5213/5214/521M		80			
	UNR521N/521T		80	400		
	UNR5210*/5215*/5216*/5217*		160	460		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
		$I_C = 10 \text{ mA}, I_B = 1.5 \text{ mA}$				
Output voltage high-level	V_{OH}	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	V_{OL}	$V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V
		$V_{CC} = 5 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1 \text{ k}\Omega$				
		$V_{CC} = 5 \text{ V}, V_B = 10 \text{ V}, R_L = 1 \text{ k}\Omega$				
		$V_{CC} = 5 \text{ V}, V_B = 6.0 \text{ V}, R_L = 1 \text{ k}\Omega$				
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Input resistance	R_i		-30%	0.51	+30%	k Ω
				1.0		
				2.2		
				4.7		
				10		
				22		
				47		
				UNR5218		
UNR5219						
UNR521M/521V						
UNR5216/521F/521L/521N UNR521Z						
UNR5211/5214/5215/521K						
UNR5212/5217/521T						
UNR5210/5213/521D/521E						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

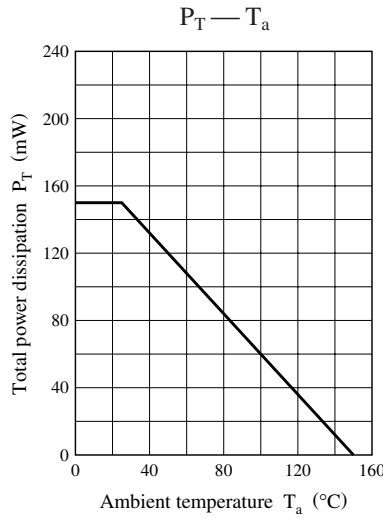
2. *: Rank classification

Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

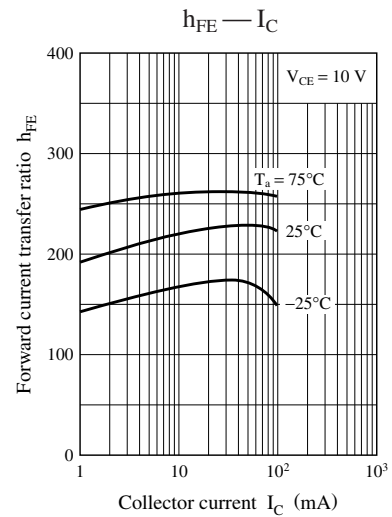
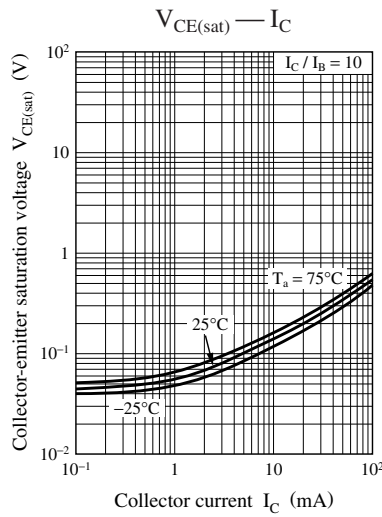
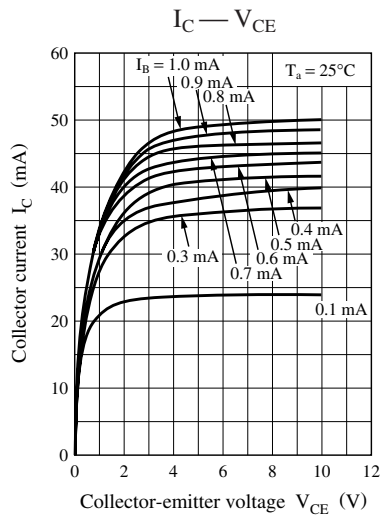
■ Electrical Characteristics (continued) $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

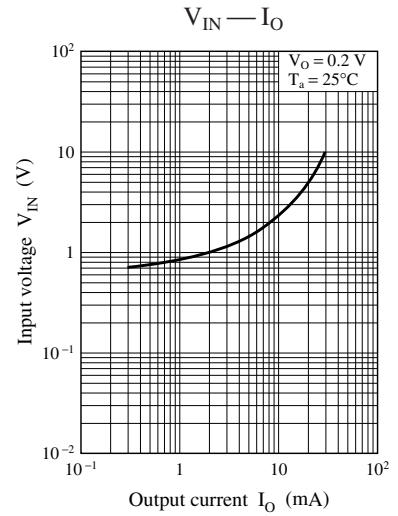
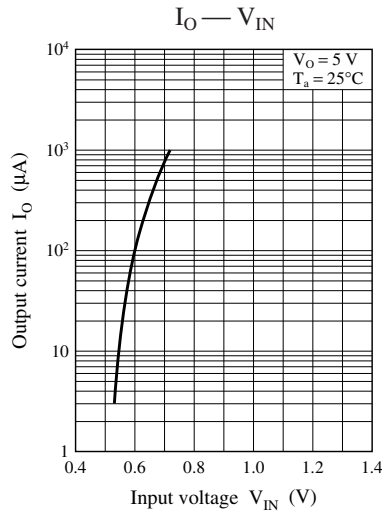
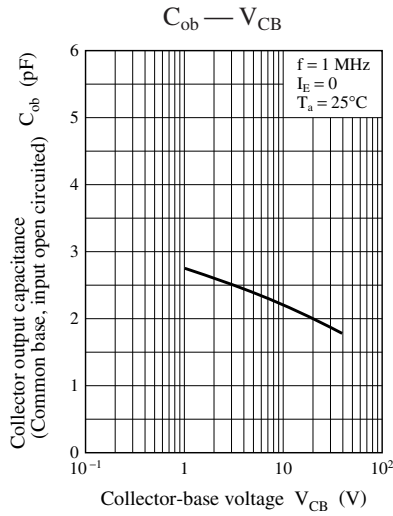
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Resistance ratio	UNR521M	R_1/R_2			0.047		—
	UNR521N				0.1		
	UNR5218/5219			0.08	0.10	0.12	
	UNR521Z				0.21		
	UNR5214			0.17	0.21	0.25	
	UNR521T				0.47		
	UNR521F			0.37	0.47	0.57	
	UNR521V				1.0		
	UNR5211/5212/5213/521L			0.8	1.0	1.2	
	UNR521K			1.70	2.13	2.60	
	UNR521E			1.70	2.14	2.60	
	UNR521D			3.7	4.7	5.7	

Common characteristics chart

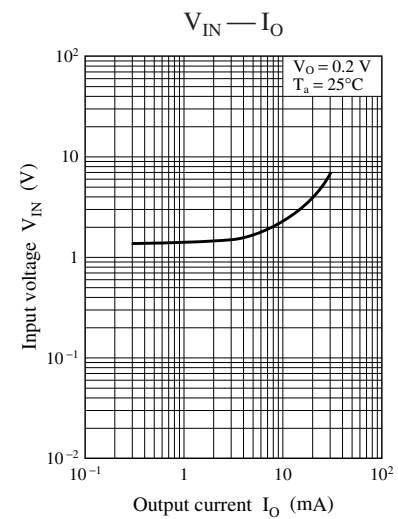
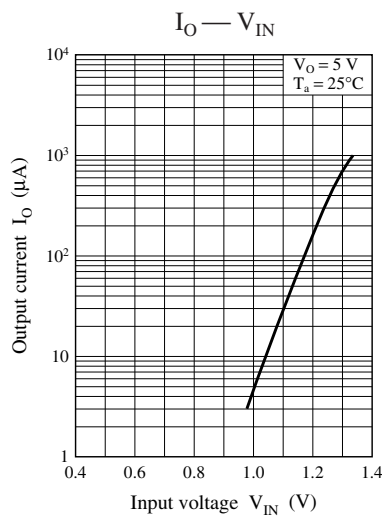
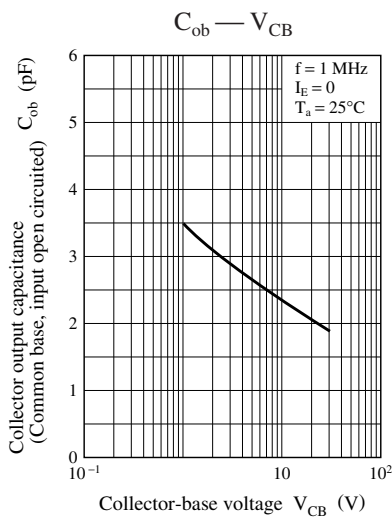
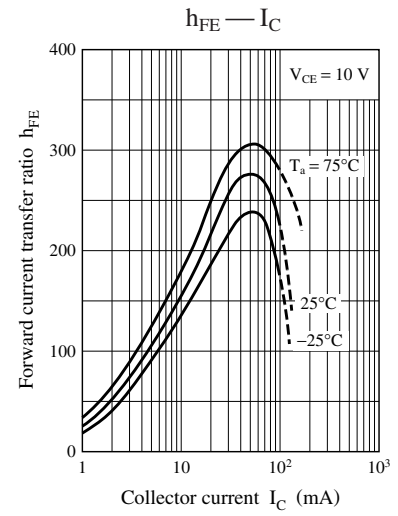
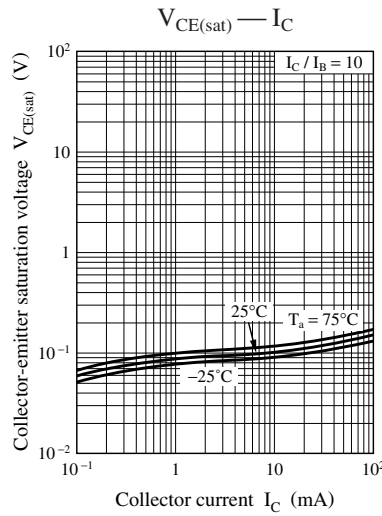
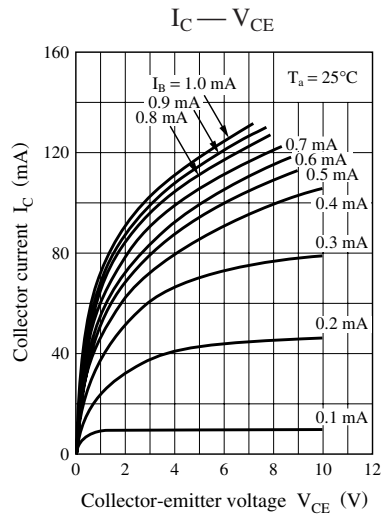


Characteristics charts of UNR5210

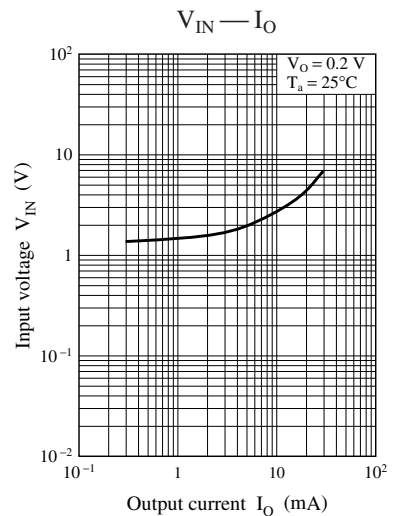
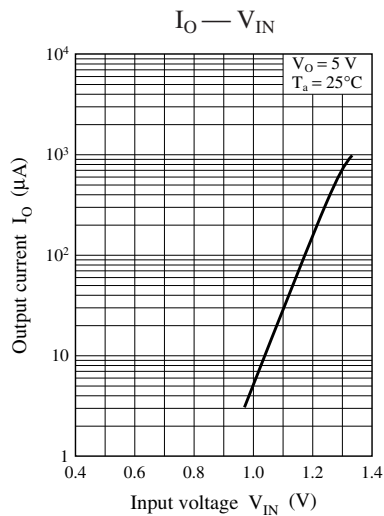
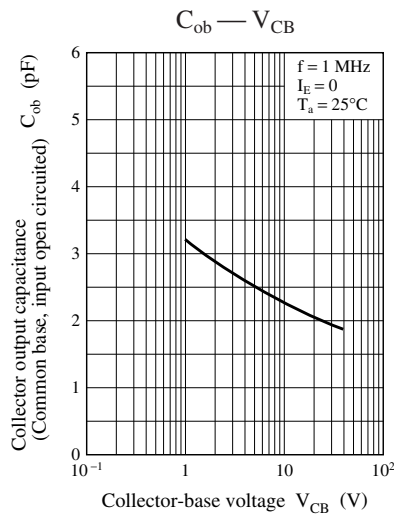
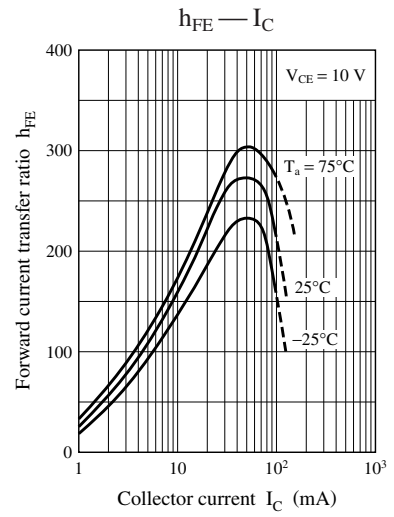
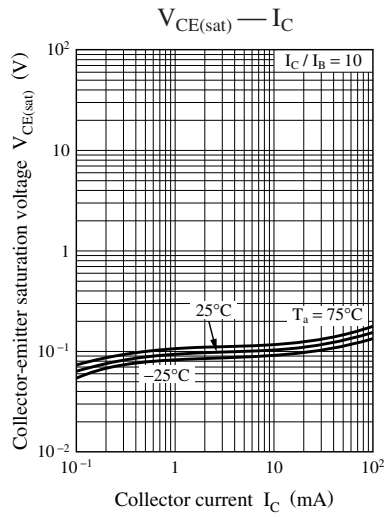
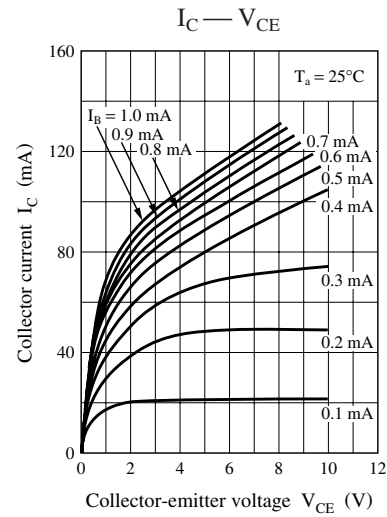




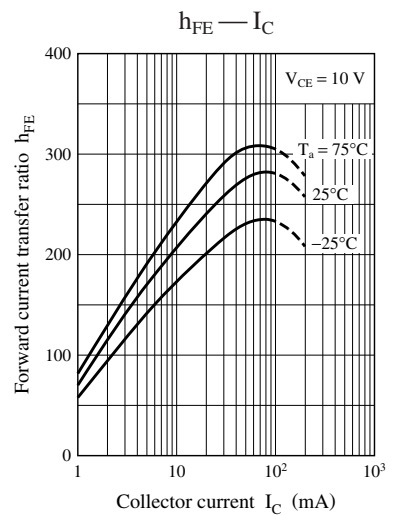
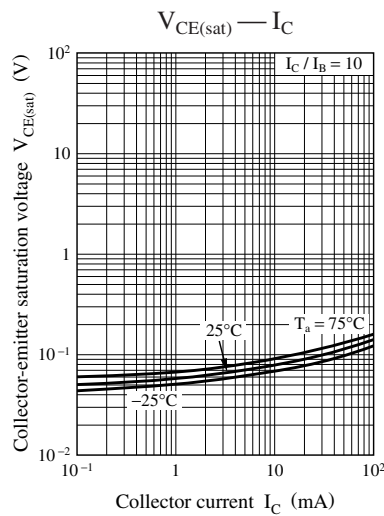
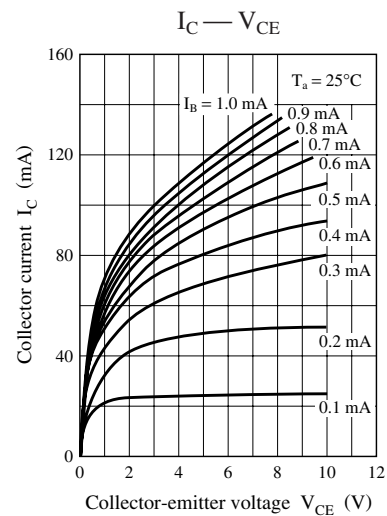
Characteristics charts of UNR5211

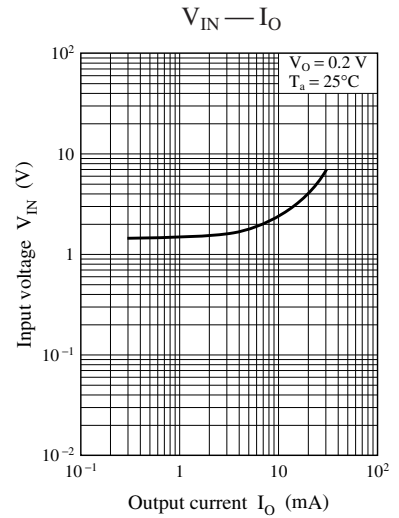
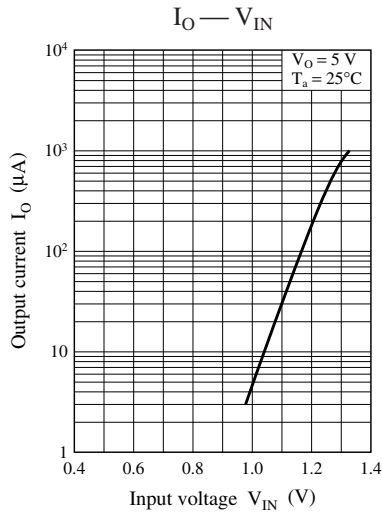
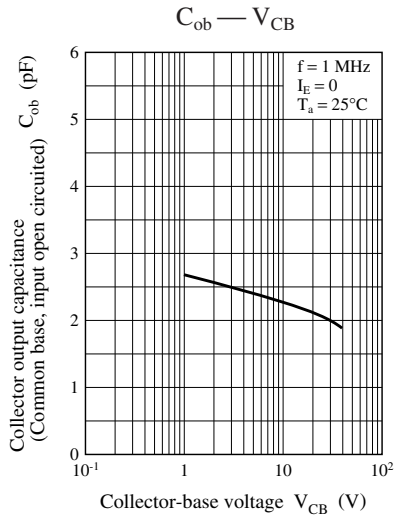


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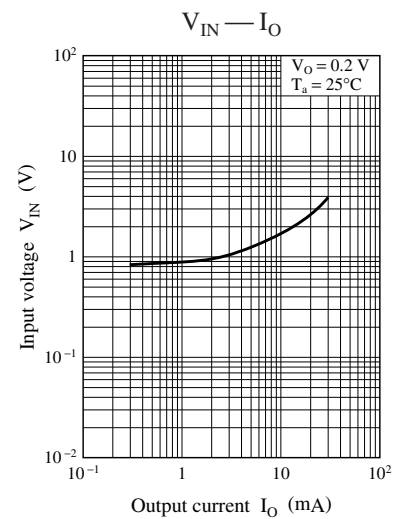
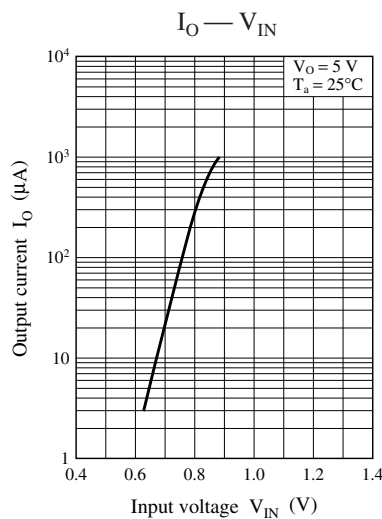
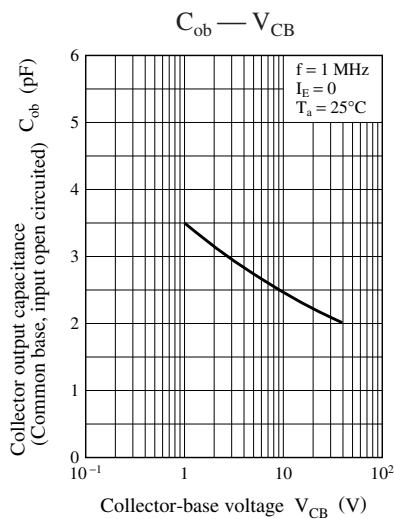
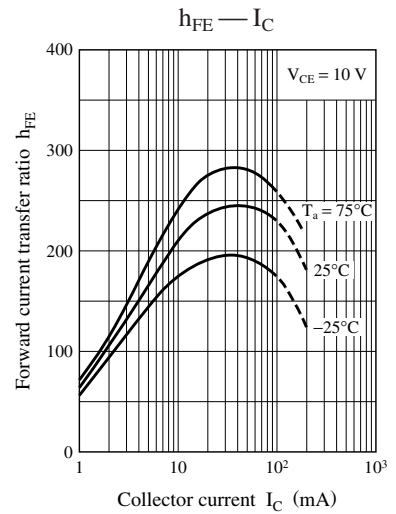
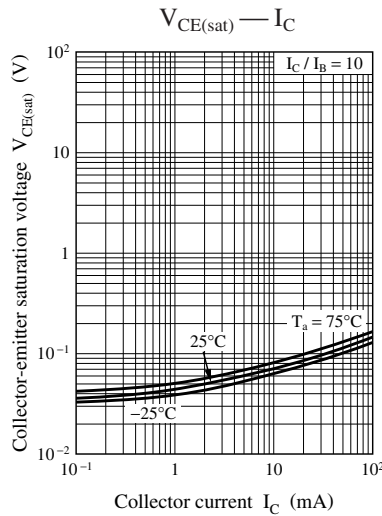
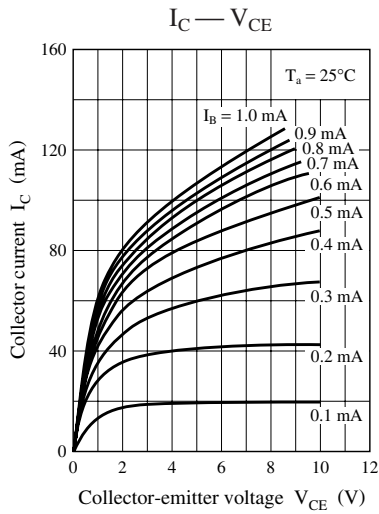


Characteristics charts of UNR5213

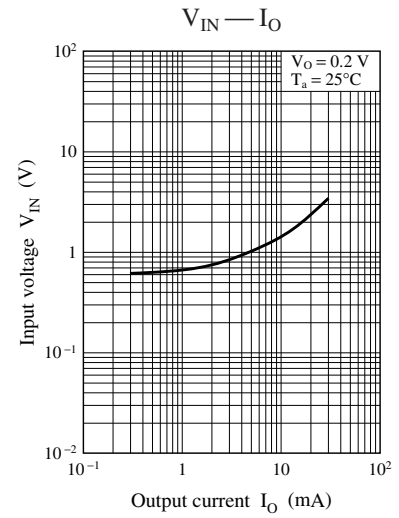
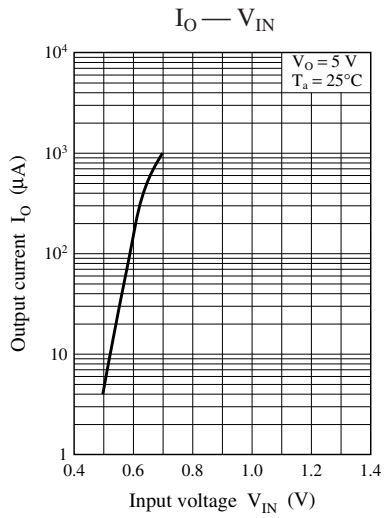
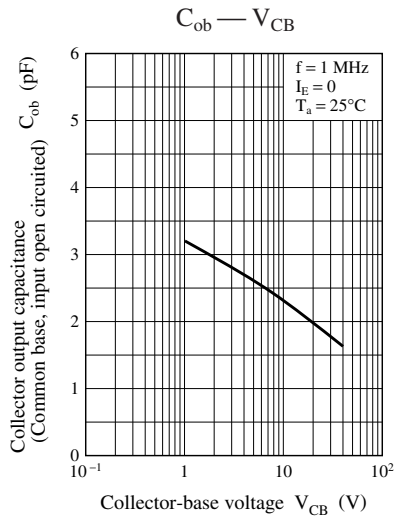
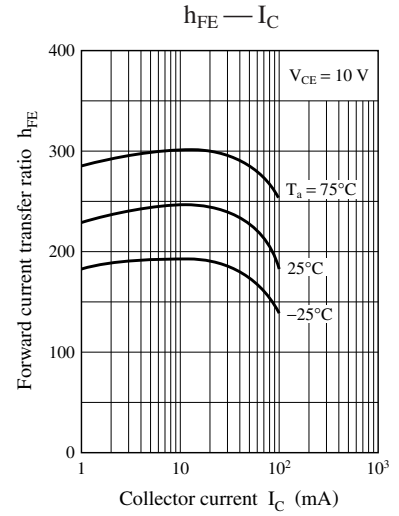
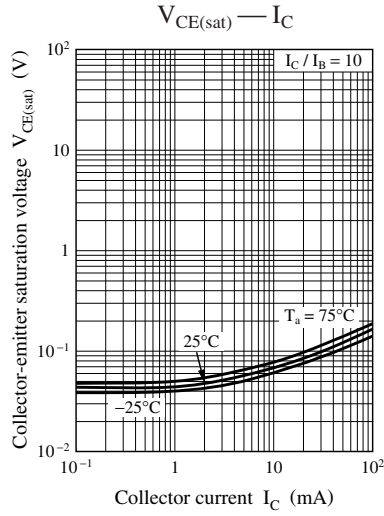
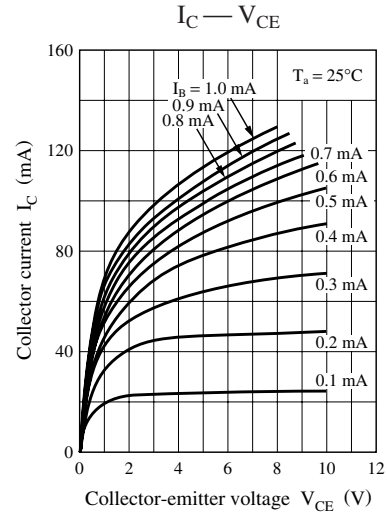




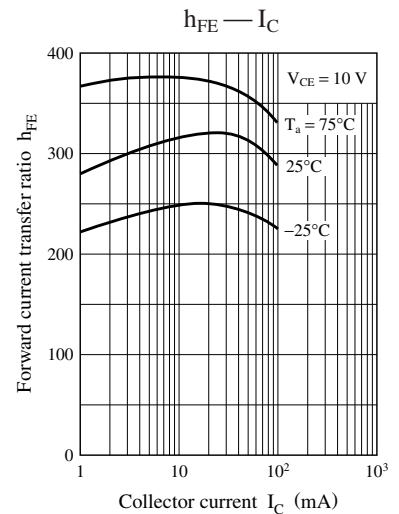
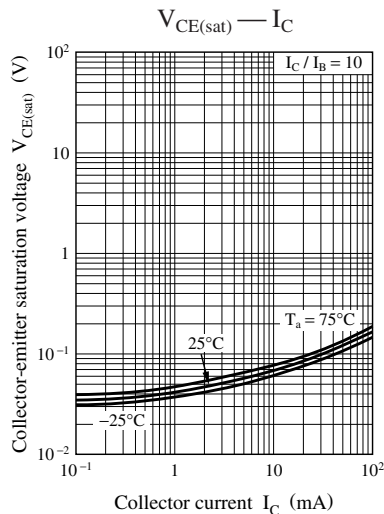
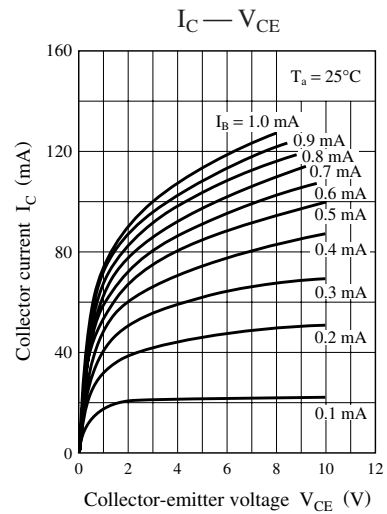
Characteristics charts of UNR5214

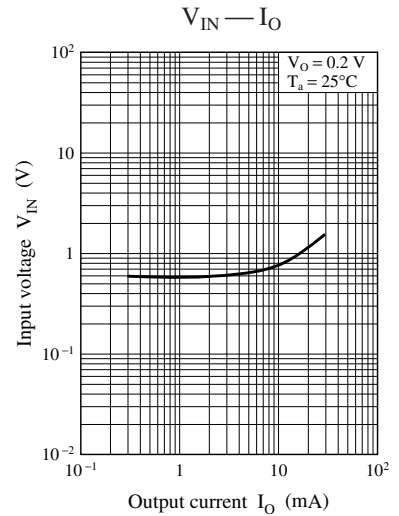
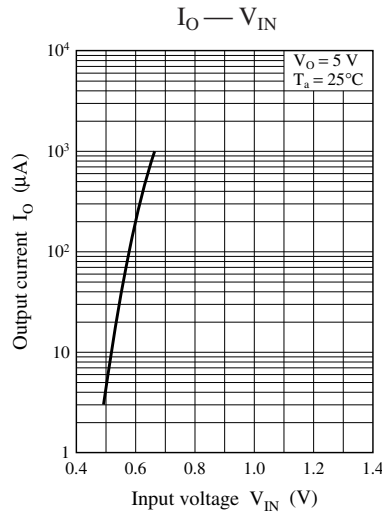
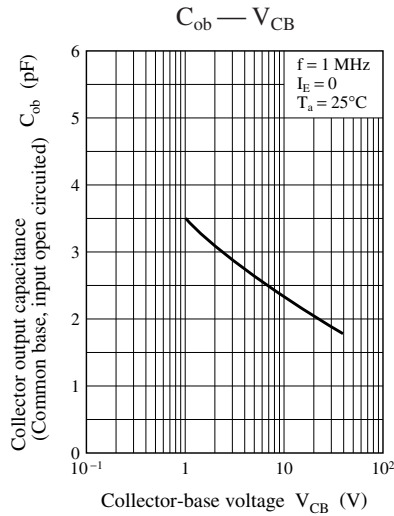


Characteristics charts of UNR5215

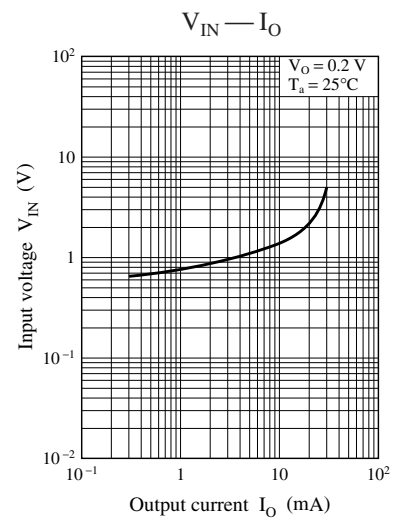
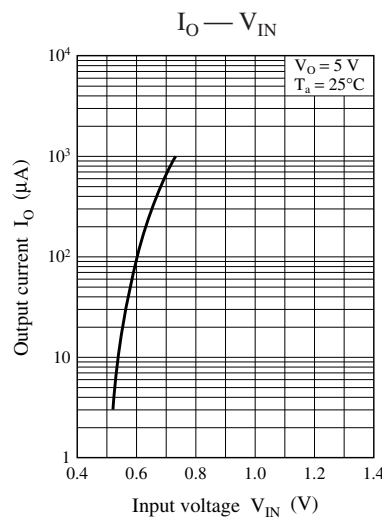
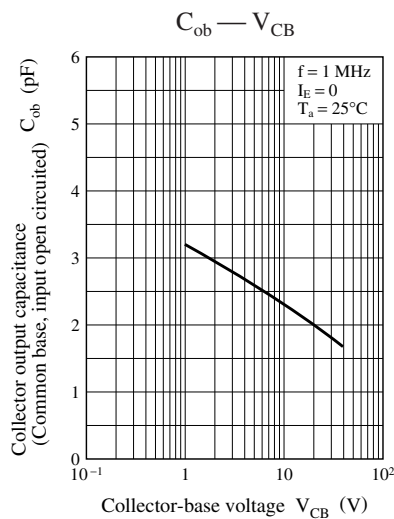
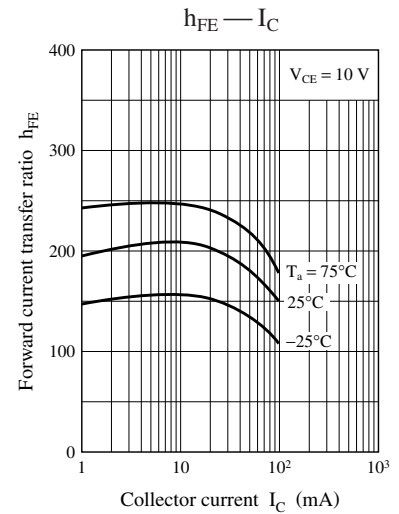
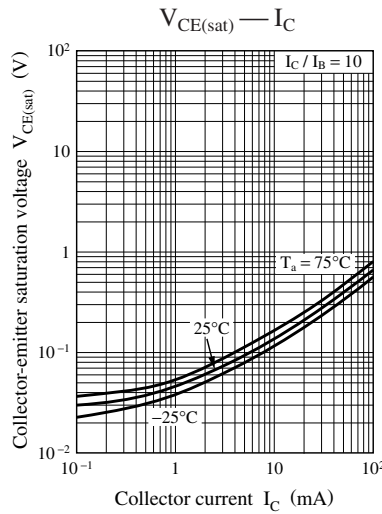
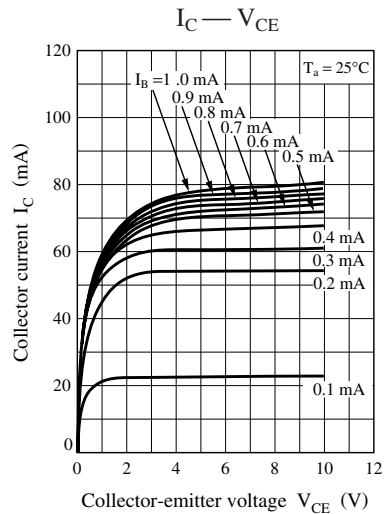


Characteristics charts of UNR5216

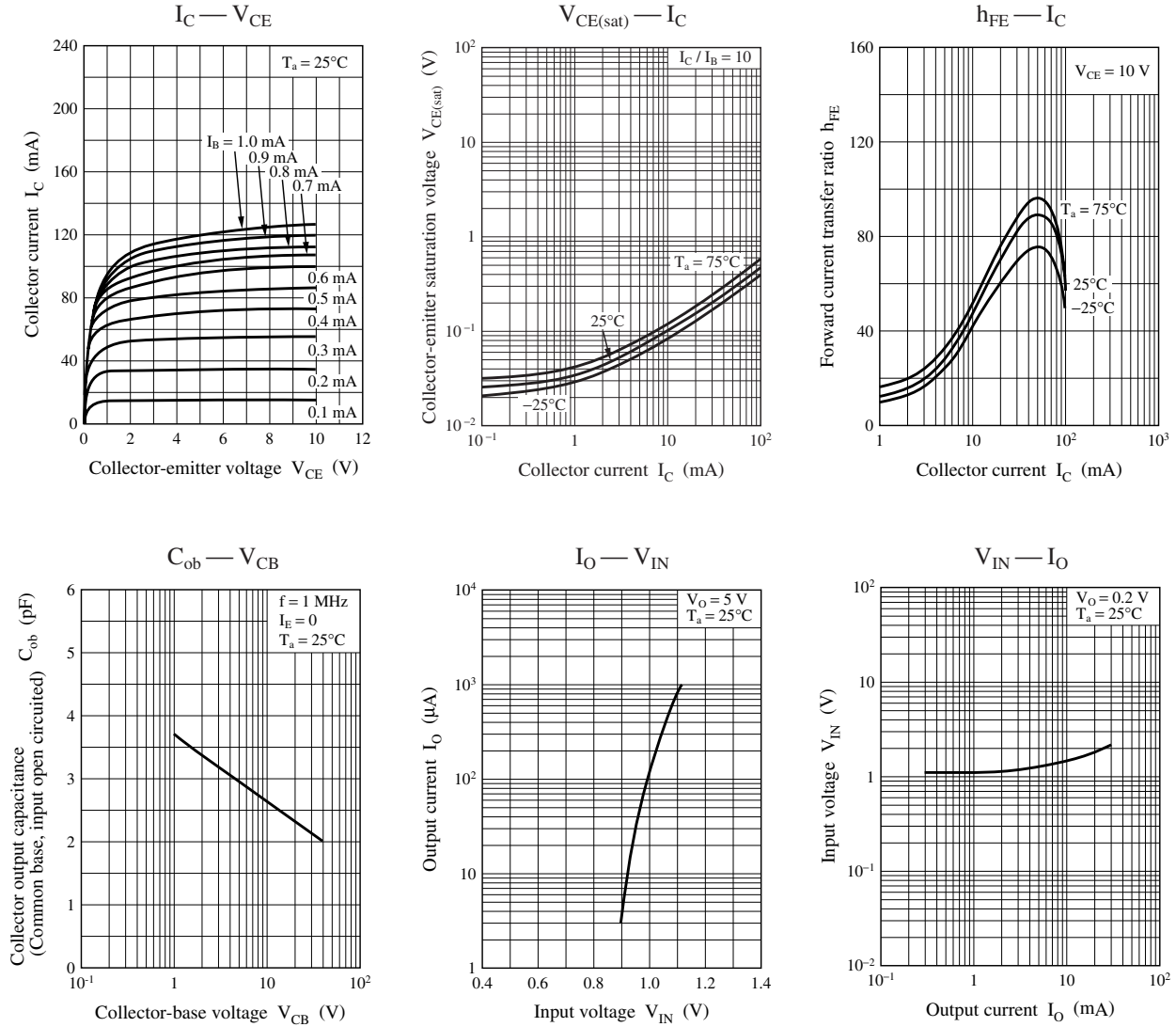




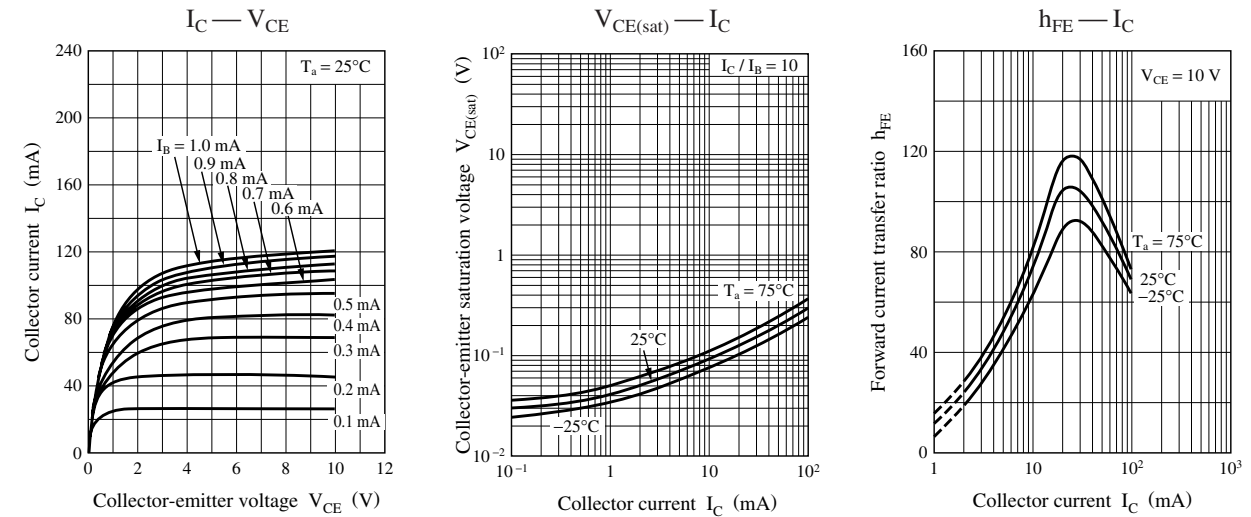
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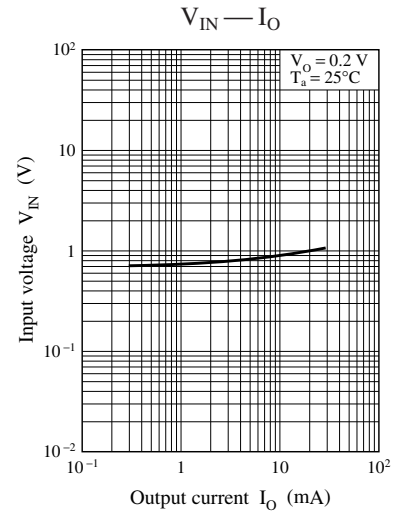
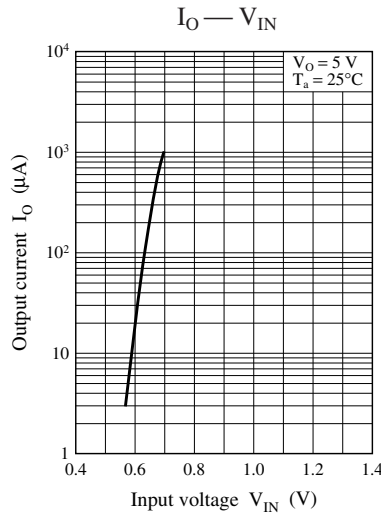
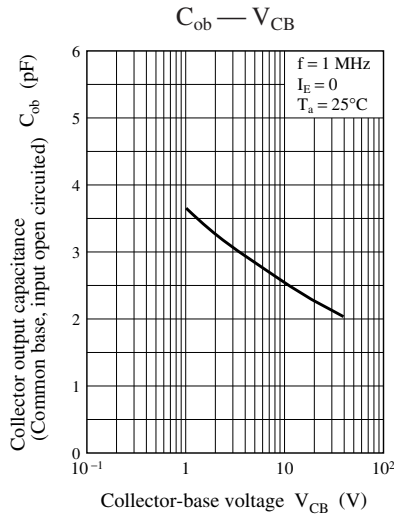


Characteristics charts of UNR5218

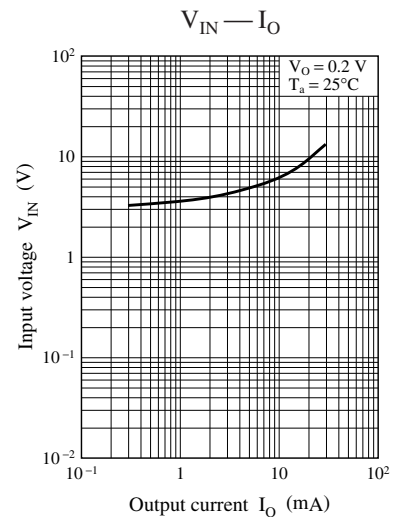
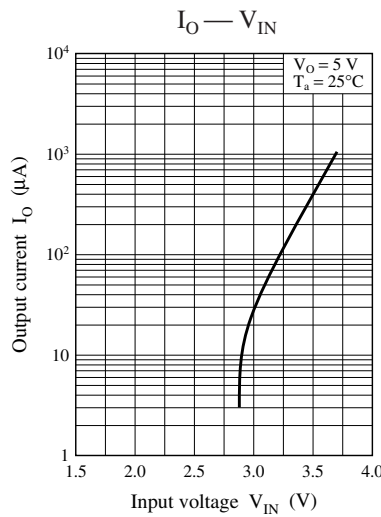
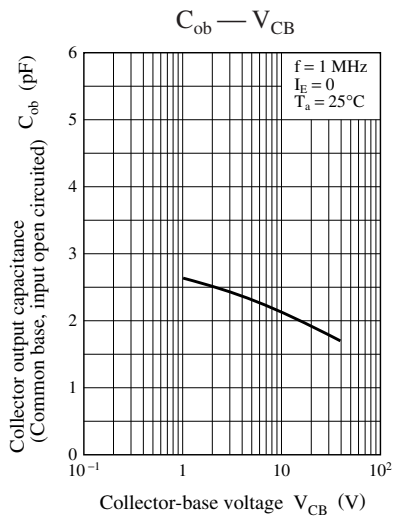
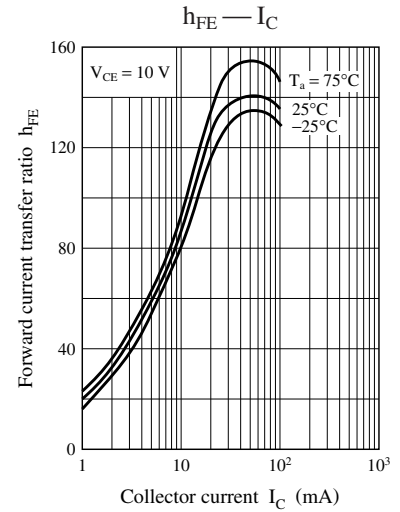
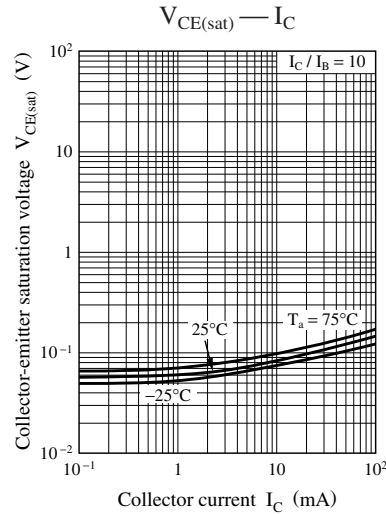
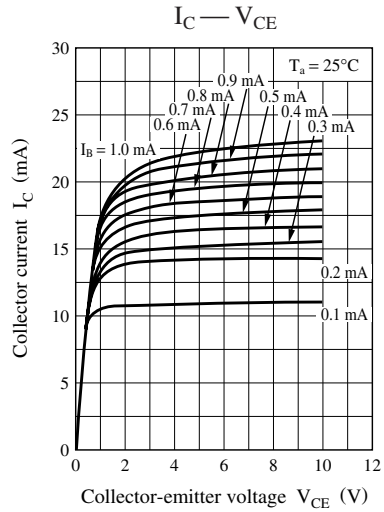


Characteristics charts of UNR5219

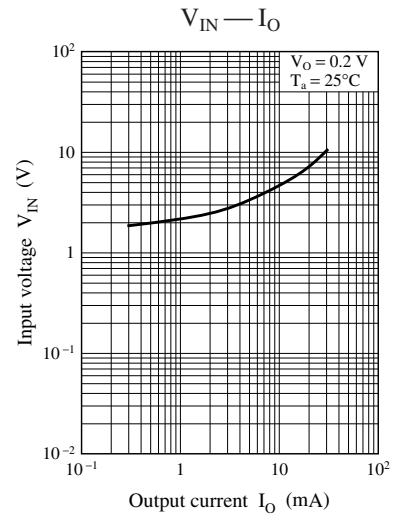
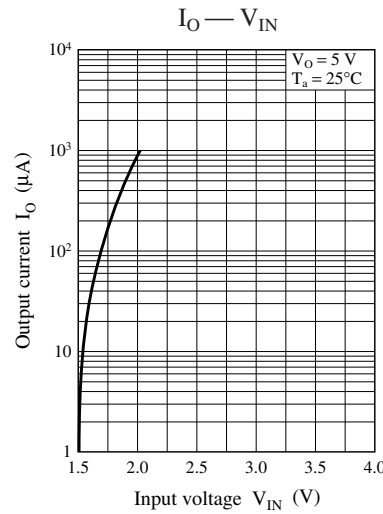
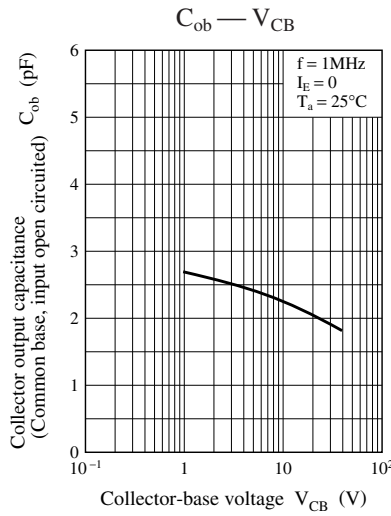
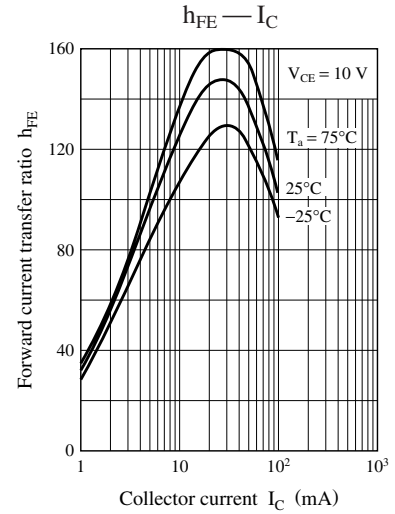
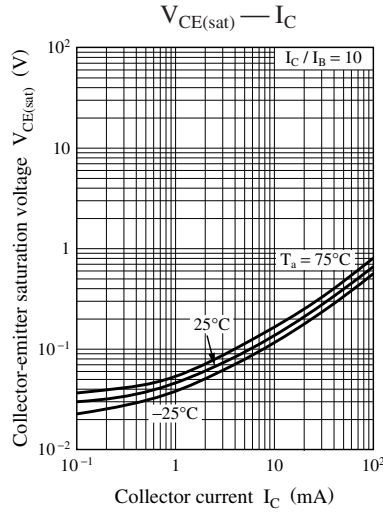
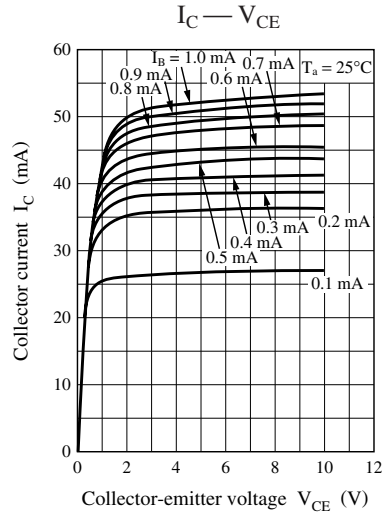




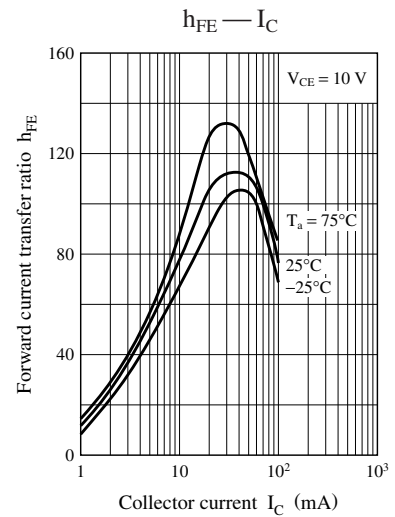
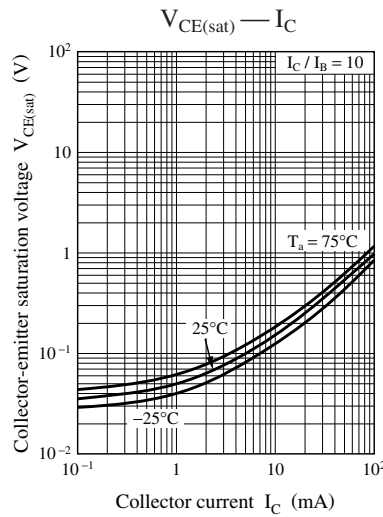
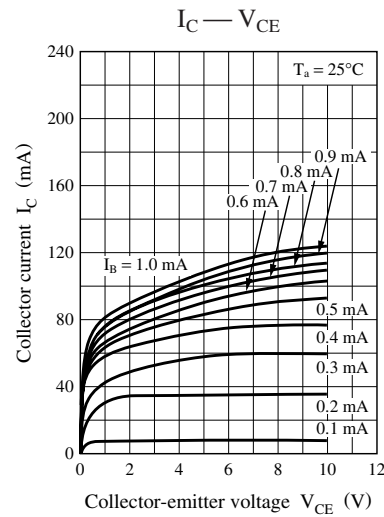
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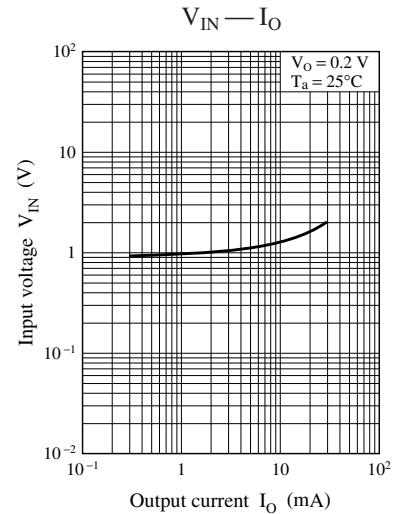
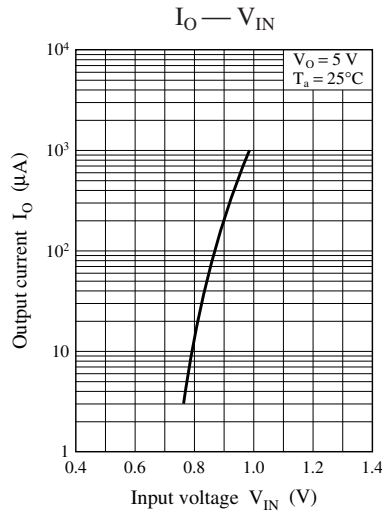
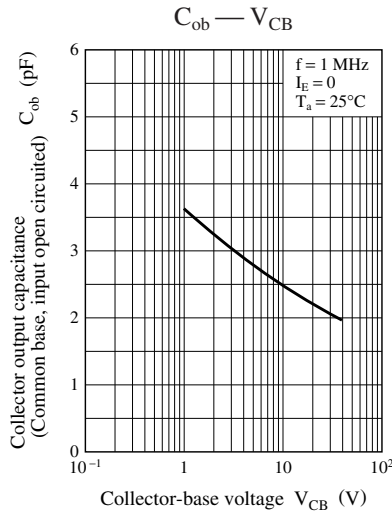


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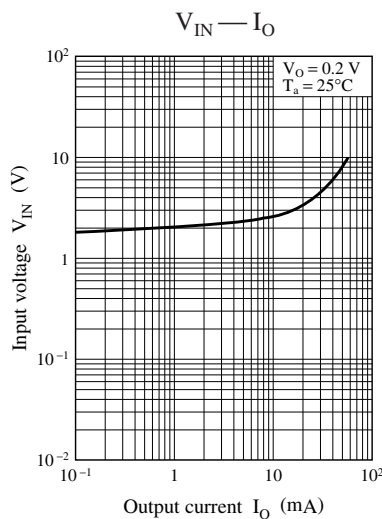
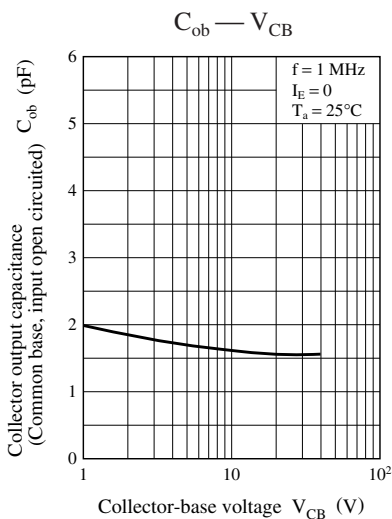
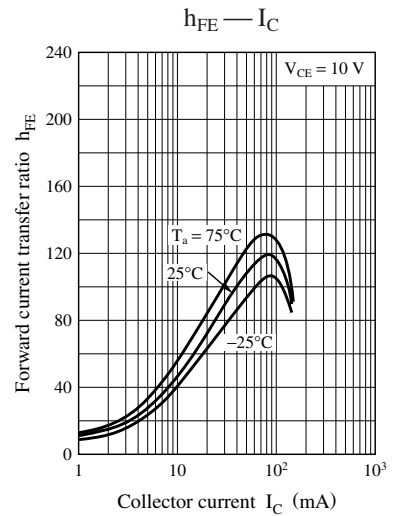
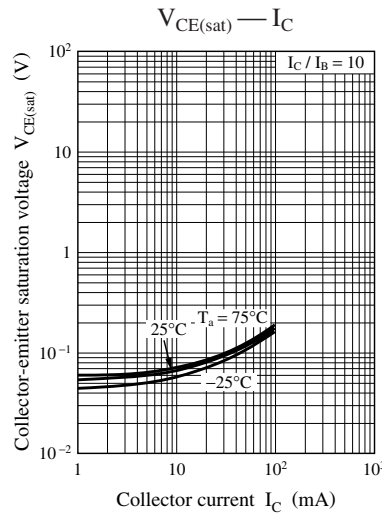
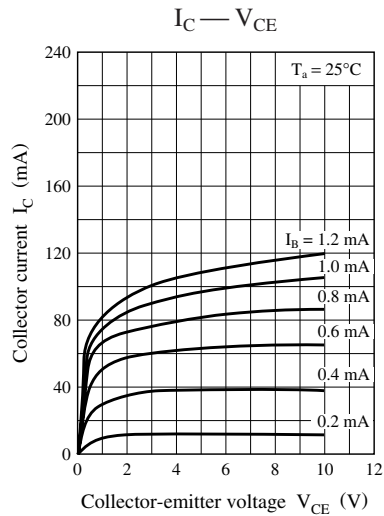


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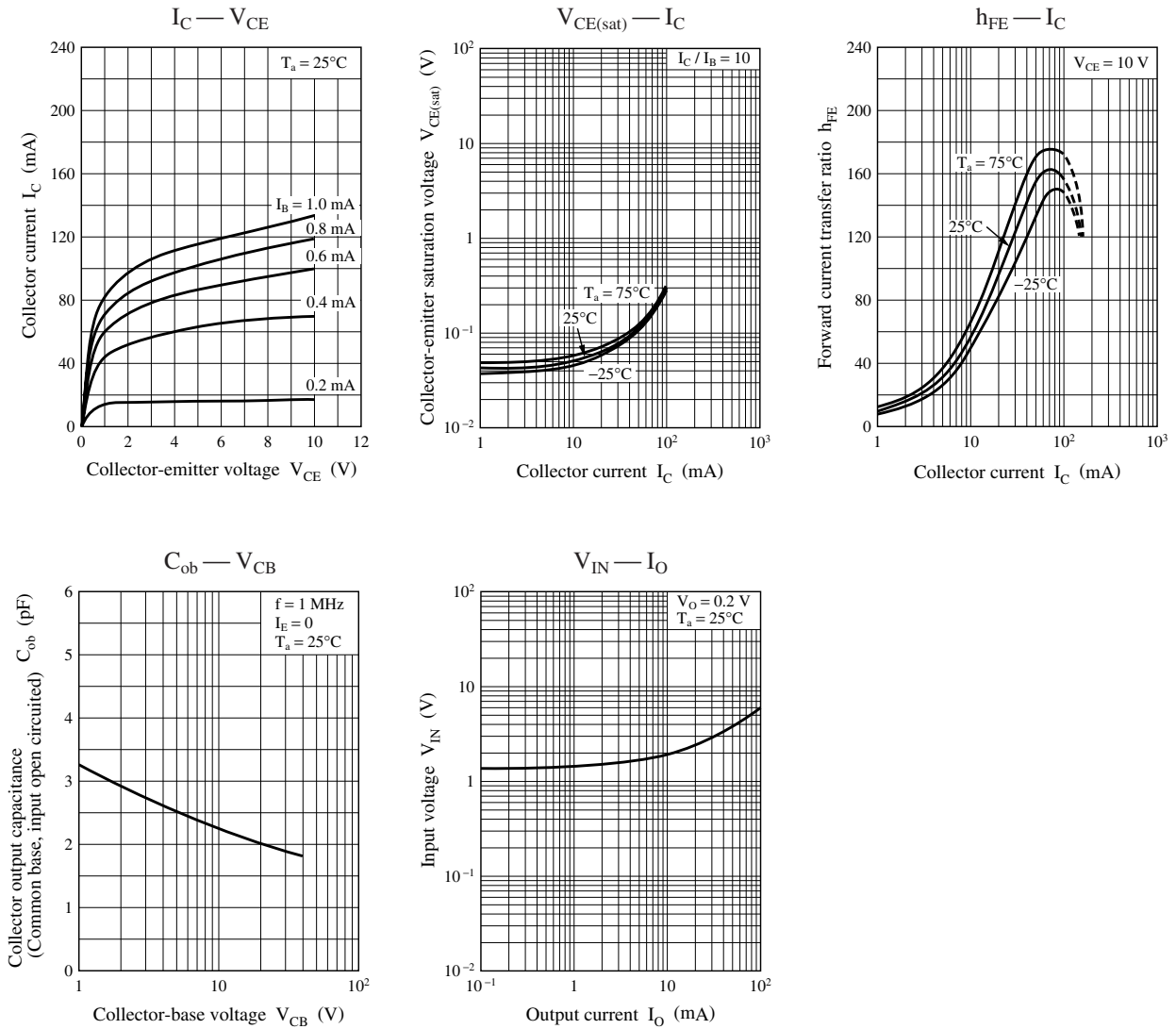




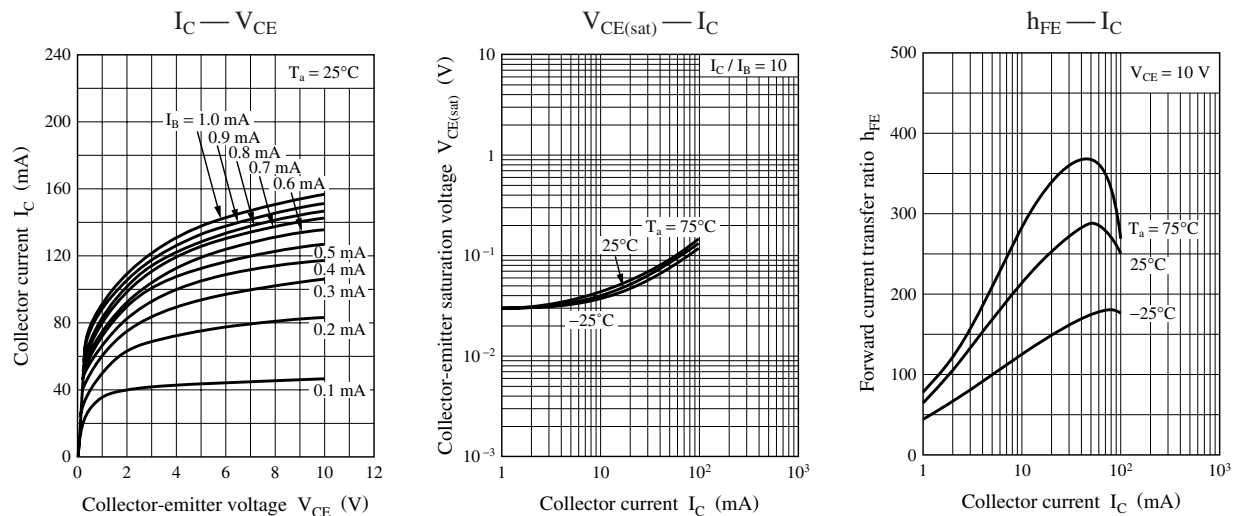
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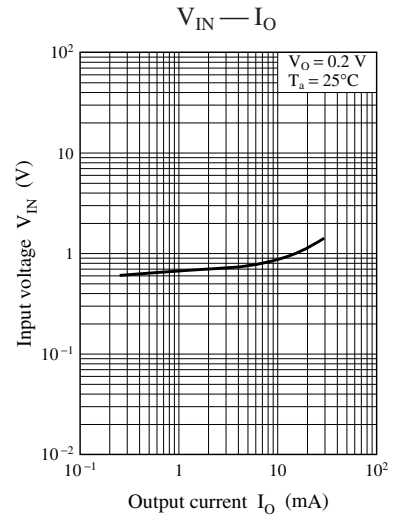
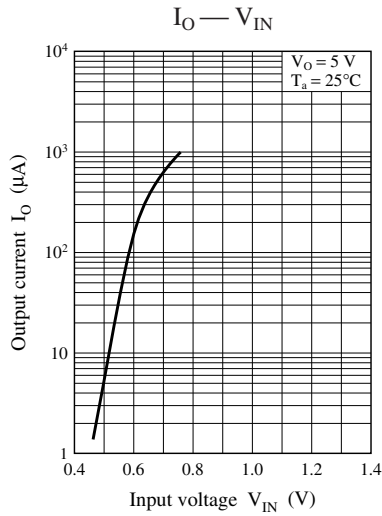
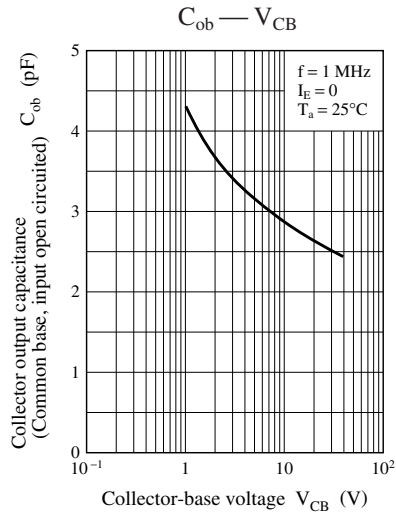


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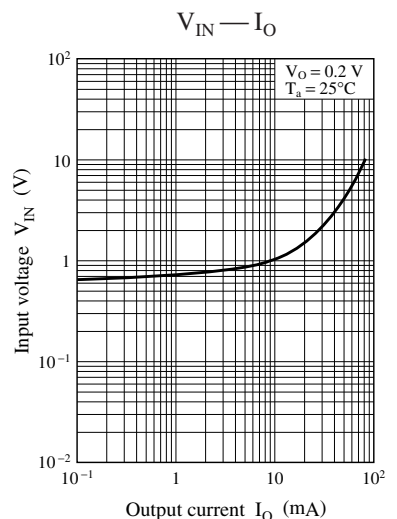
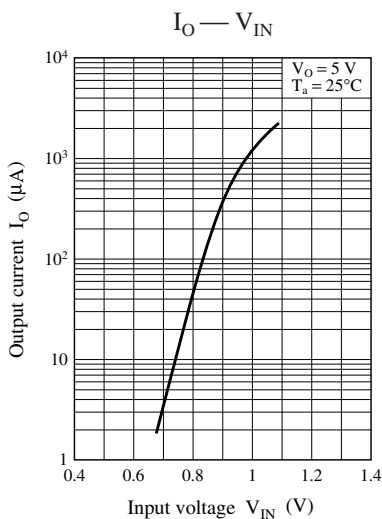
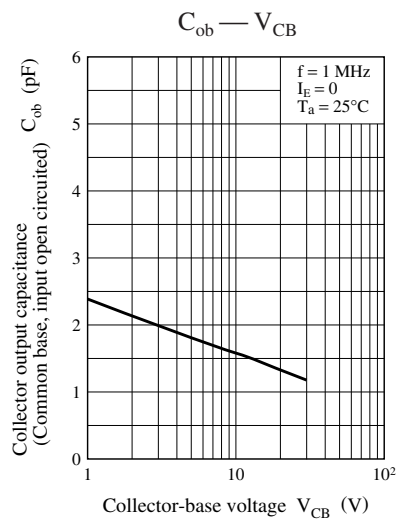
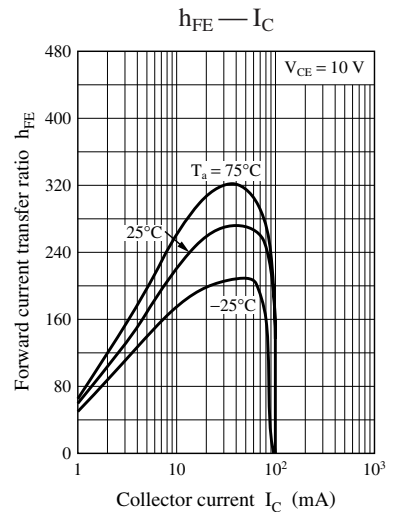
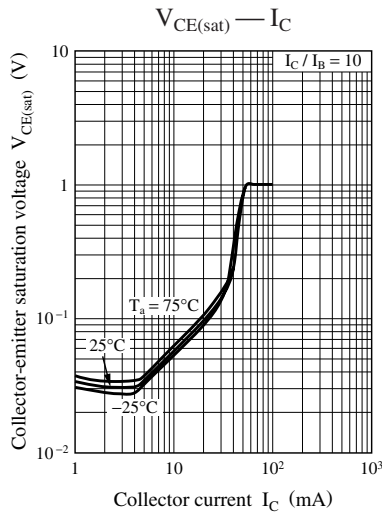
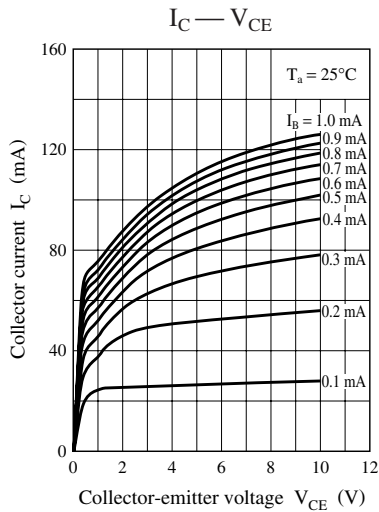


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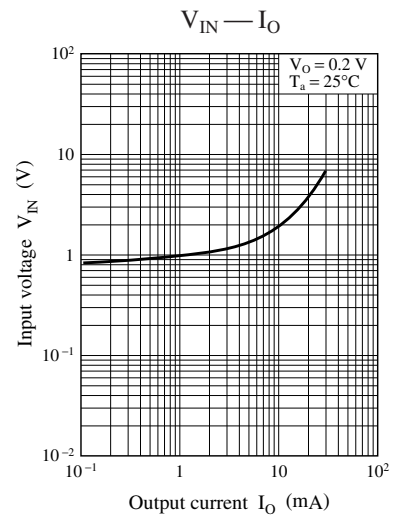
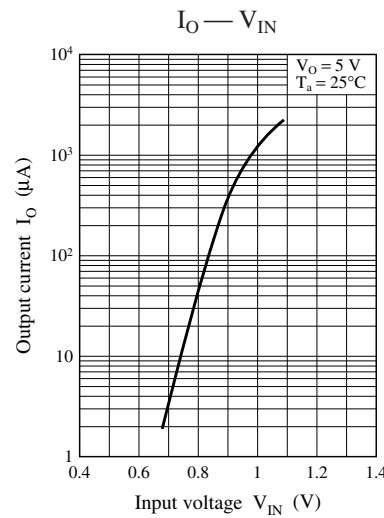
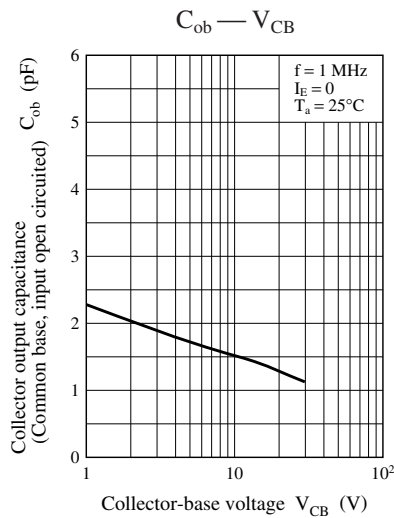
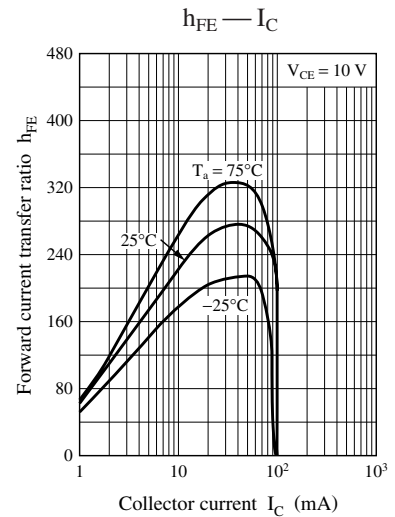
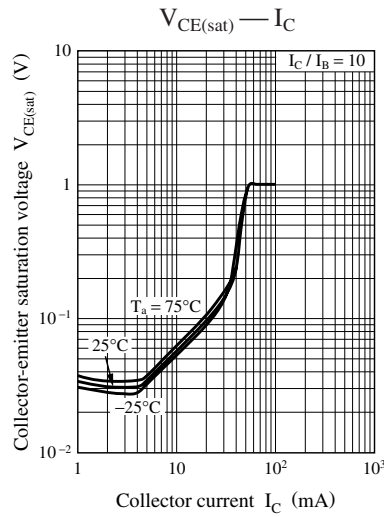
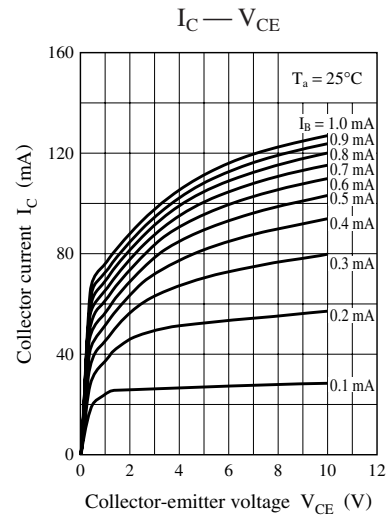




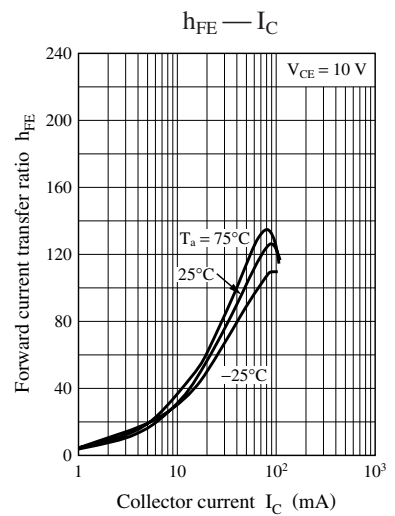
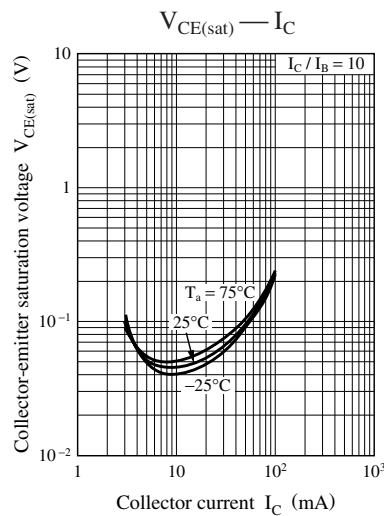
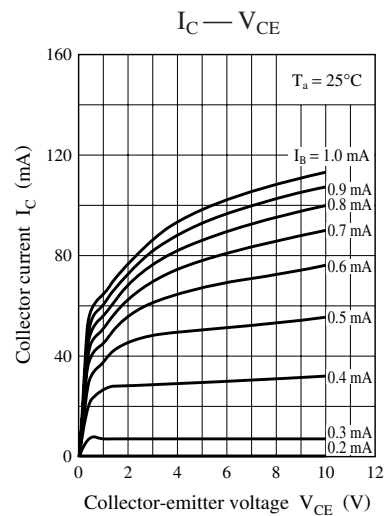
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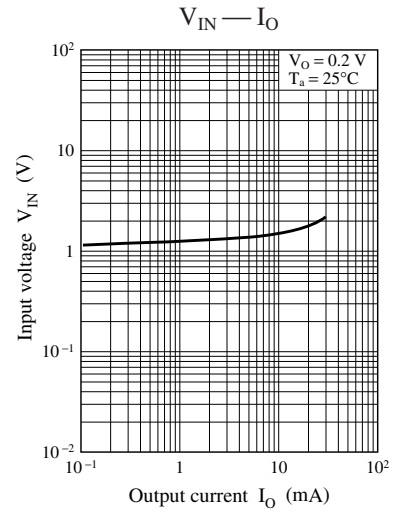
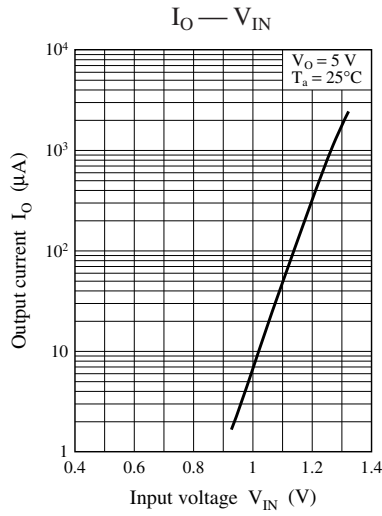
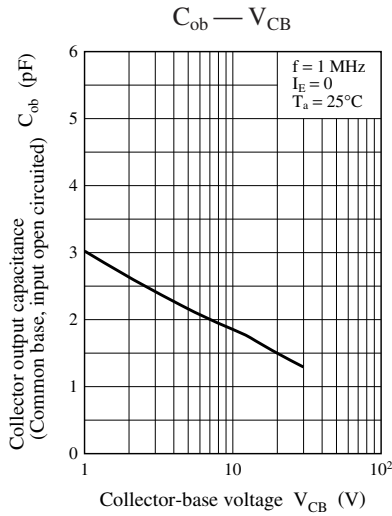


Characteristics charts of UNR521T

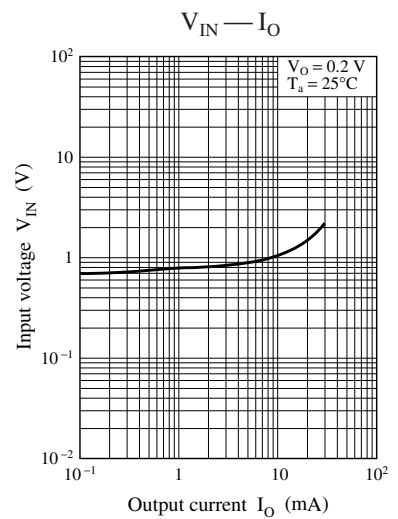
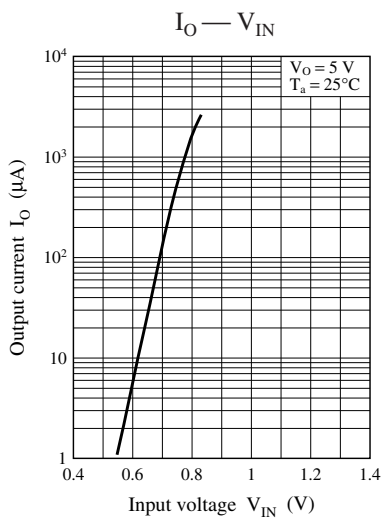
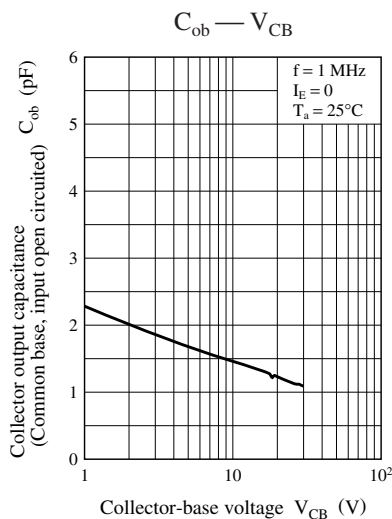
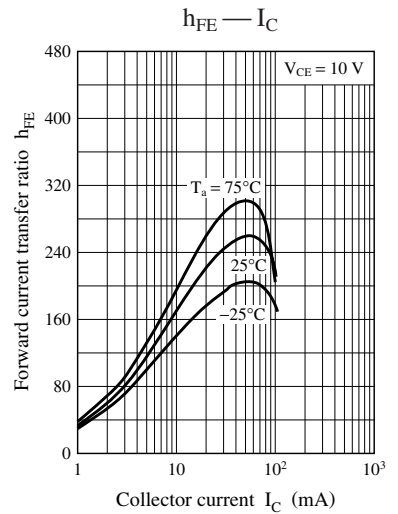
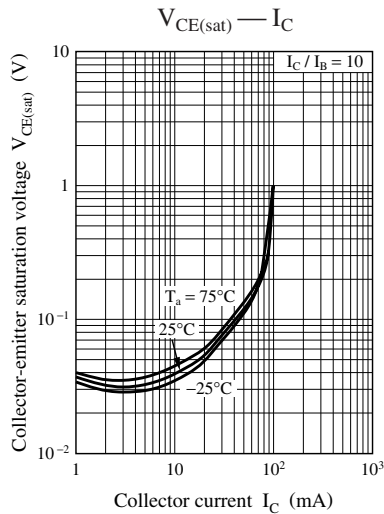
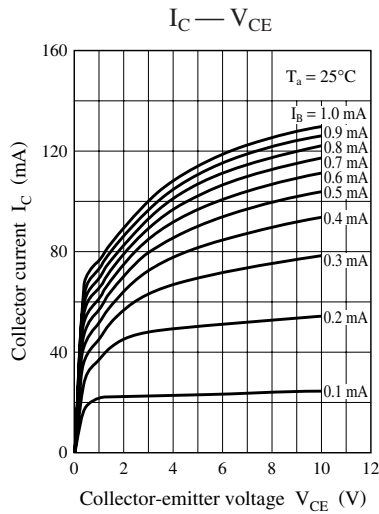


Characteristics charts of UNR521V





Characteristics charts of UNR521Z



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